Time	Presenter	Institute	Title of Presentation
	Session 1	**April 23rd**	
2:00 - 2:20pm	Beatriz Noheda	University of Groningen, Netherland	Operando studies of the interplay between ferroelectricity and electrochemistry in all-oxide MIM Hf_0.5Zr_0.5O_2 heterostructures
2:30 - 2:50pm	Nick Barrett	CEA-Saclay, Paris, France	Oxygen vacancies in hafnia-based ferroelectric capacitors
3:00 - 3:20pm	Martina Müller	Universität Konstanz, Germany	Defect and interface chemistry in ferroelectric HfO2 explored by HAXPES
	Session 2	**April 30th**	
2:00 - 2:20pm	Thanasis Dimoulas	Demokritos, Athens, Greece	Metastable ferroelectricity in scaled HZO induced by depolarizing fields: a phenomenological Landau-Ginzburg approach
2:30 - 2:50pm	Jordan Bouaziz/B. Vilquin	Université de Lyon, Lyon, France	Tracking polarization loss and imprint during electrical tests in sputtered TiN/HZO/TiN capacitors
3:00 - 3:20pm	Alex Hsain/Jacob Jones	NC State, Raleigh, USA	The Effect of Vacuum Breaking on Properties of HfO2-ZrO2 binary system capacitors
	Session 3	**May 7th**	
2:00 - 2:20pm	Alfred Kersch	Univ. of Appl. Sciences, Munich, Germany	Oxygen vacancies in HfO2/ZrO2 and impact on the formation of the ferroelectric phase
2:30 - 2:50pm	Lucian Pintilie	NIMP, Magurele, Romania	Structural investigations of HZO films and connection with macroscopic electrical properties
3:00 - 3:20pm	P. Buragohain/A. Gruverman	UN Lincoln, Nebraska, USA	Nanoscale studies of imprint behavior in ferroelectric La:HfO2 capacitors
	Session 4	**May 14th**	
2:00 - 2:20pm	Igor Stolichnov	EPFL, Lausanne, Switzerland	How do ferroelectric hafnium switch? Insight from nanoscopic analysis by PFM.
2:30 - 2:50pm	F. Berg/U. Boettger	RWTH Aachen, Germany	Effects of Moisture in Ferroelectric Switching HfOx
3:00 - 3:20pm	Sayeef Salahuddin	UC Berkeley, California, USA	Ferroelectricity and Negative Capacitance in Ultra-thin Layers of HfO2 Based Fluorite Oxides
	Session 5	**May 21th**	
2:00 - 2:20pm	Min Hyuk Park	Pusan National University	Interfacial engineering as a strategy to improve remanent polarization of Hf0.5Zr0.5O2 thin film
2:30 - 2:50pm	Anna Chernikova/A. Markeev	MIPT, Moscow, Russia	Electrode-Ferroelectric Interface engineering for improvement of HfO2-based FeRAM memory stacks
3:00 - 3:20pm	Uwe Schroeder	Namlab, Dresden, Germany	Impact of interfacial layers on retention performance of Hf0.5Zr0.5O2 based capacitors
	Session 6	**May 28th**	
2:00 - 2:20pm	Cheol Seong Hwang	Seoul National University	Review of ferroelectric field-effect transistors for three-dimensional storage applications
2:30 - 2:50pm	Laurent Grenouillet	LETI, Grenoble, France	HfO2-based BEOL-integrated ferroelectric capacitor for ultra low power FeRAM
3:00 - 3:20pm	Franz Müller/Wenke Weinreich	FhG IPMS-CNT, Dresden, Germany	Characterization of Percolation Paths of FeFETs
3:30 - 3:50pm	Sourav Dutta/Suman Datta	Notre Dame, IN, USA	Monolithic 3D Integration of Ferroelectric FET for Accelerating Compute-In-Memory